

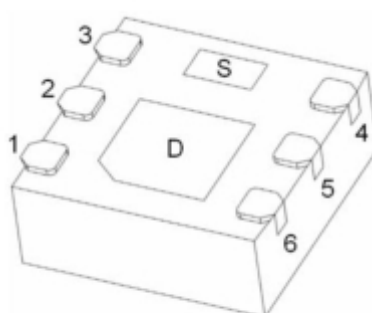
## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	11mΩ@4.5V	9A
	20mΩ@2.5V	

## Feature

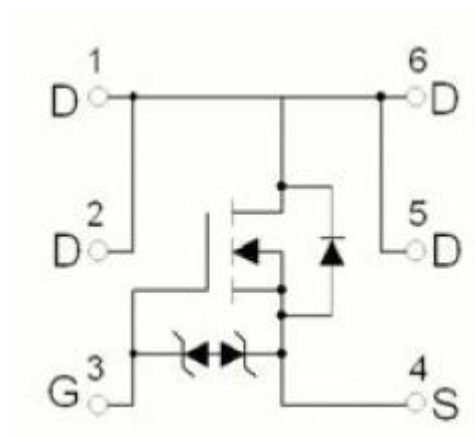
- $R_{DS(ON)}$  (at  $V_{GS} = 4.5V$ ) < 23 mΩ
- $R_{DS(ON)}$  (at  $V_{GS} = 2.5V$ ) < 38 mΩ
- Fast Switching
- ESD Protected

## Package



DFNWB2\*2-6L

## Circuit diagram



## Marking



**20N11K    =Device Code**

## Absolute maximum ratings

( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

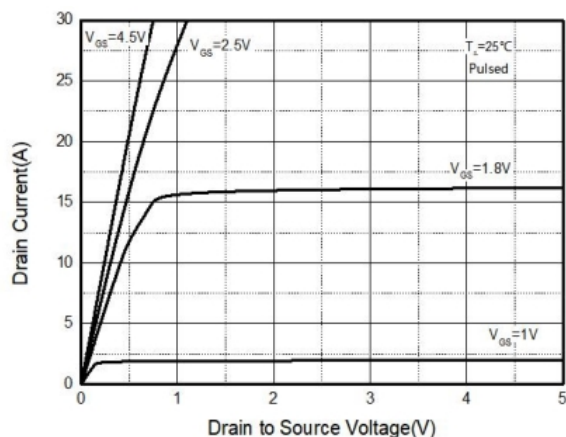
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current	$I_D$	9	A
Pulsed Drain Current	$I_{DM}$	36	A
Power Dissipation	$P_D$	2.1	W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	59	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^{\circ}\text{C}$

## Electrical characteristics

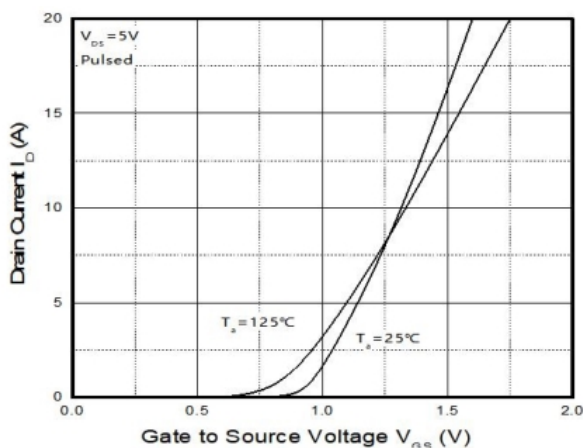
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Parameter						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250mA$	20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 100$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250mA$	0.4	0.65	1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 4A$		11	23	m $\Omega$
		$V_{GS} = 2.5V, I_D = 3A$		20	38	
Dynamic Parameters						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$		982		pF
Output Capacitance	$C_{oss}$			228		
Reverse Transfer Capacitance	$C_{rss}$			125		
Switching Parameters						
Total Gate Charge	$Q_g$	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 7A$		8.7		pF
Gate Source Charge	$Q_{gs}$			2.5		
Gate Drain Charge	$Q_{gd}$			3.1		
Turn-On Delay Time	$T_{d(on)}$	$V_{GS} = 4.5V, V_{DS} = 10V, R_L = 1.5\Omega, R_{GEN} = 3\Omega$		1.3		nS
Rise Time	$T_r$			2.5		
Turn-Off Delay Time	$T_{d(off)}$			28		
Fall Time	$T_f$			8		
Drain-Source Diode Characteristics						
Diode Forward Voltage <sup>(2)</sup>	$V_{SD}$	$I_S = 1A, V_{GS} = 0V$			1.2	V

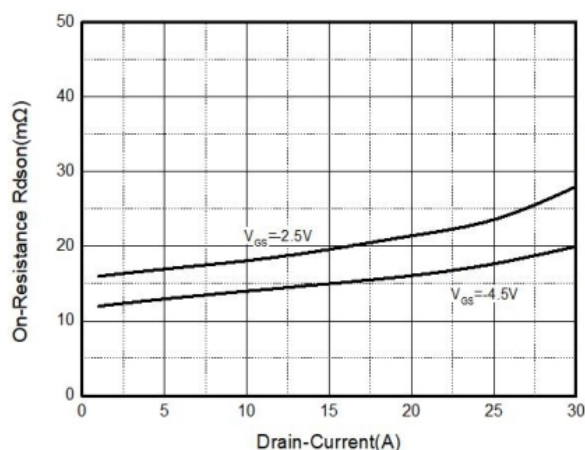
## Typical Characteristics



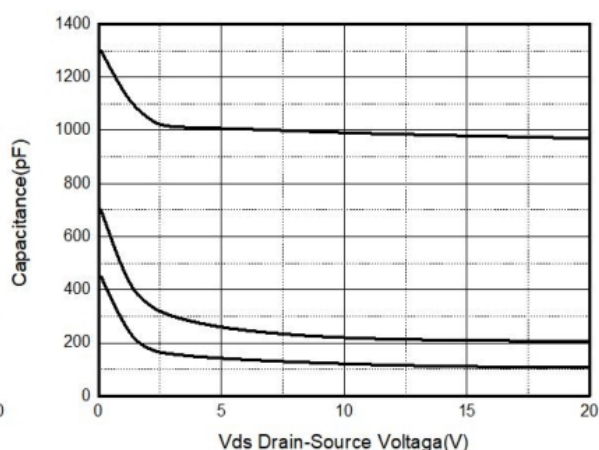
Output Characteristics



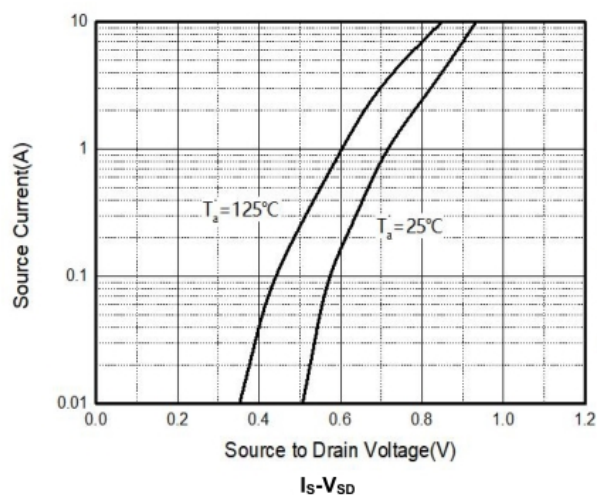
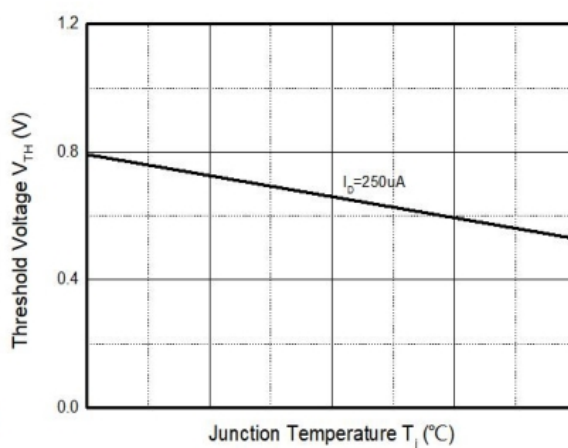
Transfer Characteristics



Drain-Source On Resistance

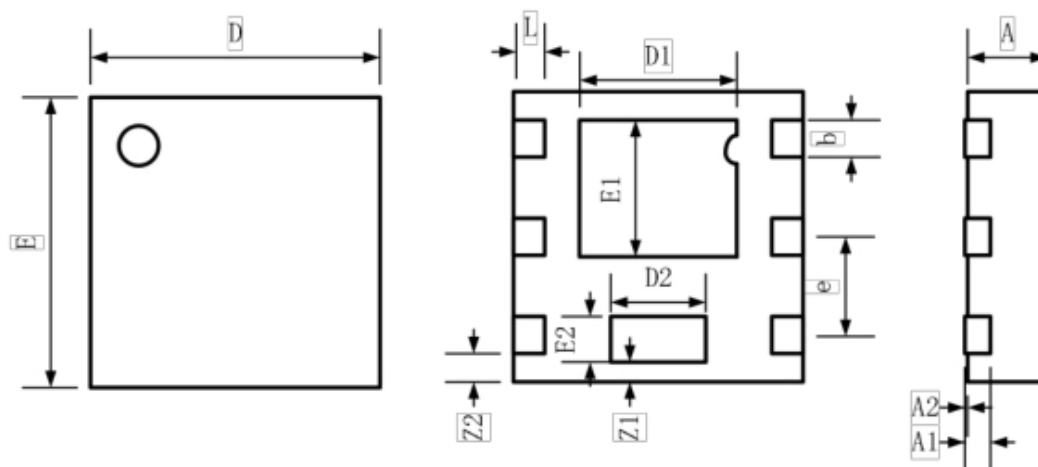


Capacitance Characteristics


 $I_S$ - $V_{SD}$ 


Threshold

## DFN2\*2-6L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D1	1.10	1.15	1.20
E1	0.90	0.95	1.00
D2	0.65	0.70	0.75
E2	0.33	0.38	0.43
L	0.225	0.275	0.325
b	0.25	0.30	0.35
e	0.65BSC		
A	0.47	0.5	0.55
A1	0.20REF		
A2	0.00		0.05
Z1	0.06	0.11	0.16
Z2	0.15	0.20	0.25